

Silicon PNP Power Transistor

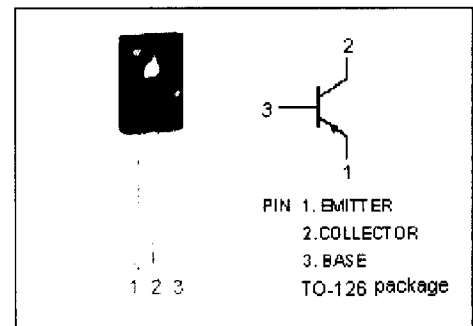
BD726

DESCRIPTION

- DC Current Gain-
 : $h_{FE} = 40 @ I_C = -0.5A$
- Collector-Emitter Breakdown Voltage -
 : $V_{(BR)CEO} = -120V(\text{Min})$
- Complement to type BD725

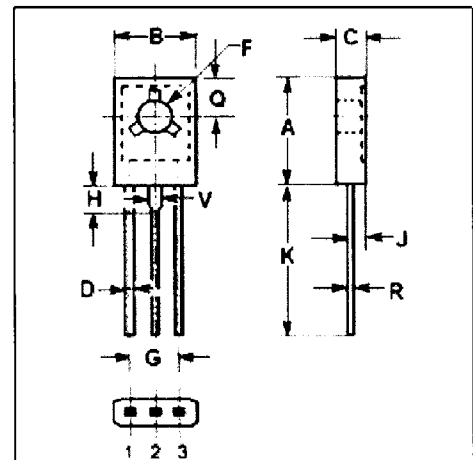
APPLICATIONS

- Designed for use in audio output and general purpose amplifier applications.



ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-7	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ C$	30	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	10.70	10.90
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	16.10	16.30
O	3.70	3.90
R	0.40	0.60
V	1.17	1.37

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.5	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	100	$^\circ C/W$

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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-120			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -2\text{A}; V_{CE} = -4\text{V}$			-1.4	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120\text{V}; I_E = 0$			-50	μA
		$V_{CB} = -60\text{V}; I_E = 0; T_C = 150^\circ\text{C}$			-1	mA
I_{CEO}	Collector Cutoff Current	$V_{CE} = -60\text{V}; I_B = 0$			-0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-0.2	mA
h_{FE-1}	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -4\text{V}$	40			
h_{FE-2}	DC Current Gain	$I_C = -2\text{A}; V_{CE} = -4\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -4\text{V}$	3			MHz

Switching Times

t_{on}	Turn-On time	$I_C = -1\text{A}; I_{B1} = -I_{B2} = -0.1\text{A}; V_{CC} = -20\text{V}$		0.1		μs
t_{off}	Turn-Off time			0.4		μs